Product data sheet

1. General description

Planar passivated AC Thyristor Triac power switch in a SOT186A (TO-220F) "full pack" plastic package with self-protective capabilities against low and high energy transients.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Full cycle AC conduction
- Isolated mounting base package
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Safe clamping capability for low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|--|--|-----|-----|-----|------|
| V_{DRM} | repetitive peak off- state voltage | | - | - | 800 | V |
| I _{TSM} | non-repetitive peak on- state current | full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5 | - | - | 120 | A |
| T _j | junction temperature | | - | - | 125 | °C |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3 | - | - | 12 | A |





| Symbol | Parameter | Conditions | M | lin | Тур | Max | Unit |
|---------------------------------------|-----------------------------------|---|---|-----|-----|-----|------|
| V_{PP} | peak pulse voltage | T _j = 25 °C; non-repetitive, off-state; Fig. 6 | - | | - | 2 | kV |
| Static chara | acteristics | | | | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$ | - | | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$ | - | | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$ | - | | - | 35 | mA |
| V _{CL} | clamping voltage | I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C | 8 | 50 | - | - | V |
| Dynamic ch | naracteristics | | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 536 V; T _j = 125 °C; exponential waveform; gate open circuit | | 000 | - | - | V/µs |
| commutating current dV _{cor} | | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit | 1 | 4 | - | - | A/ms |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1 | T1 | main terminal 1 | mb | T2—T1 |
| 2 | T2 | main terminal 2 | | G sym051 |
| 3 | G | gate | | · |
| mb | n.c. | mounting base; isolated | | |
| | | | TO-220F (SOT186A) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | | |
|--------------|---------|---|---------|--|--|--|--|--|
| | Name | Description | Version | | | | | |
| ACTT12X-800C | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A | | | | | |

ACTT12X-800C

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AC Thyristor Triac power switch

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|--------------|--------------|
| ACTT12X-800C | ACTT12X-800C |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|-----|------------------|
| V_{DRM} | repetitive peak off-state voltage | | - | 800 | V |
| I _{T(RMS)} | RMS on-state current | full sine wave; $T_h \le 57$ °C; Fig. 1; Fig. 2; Fig. 3 | - | 12 | A |
| I _{TSM} | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5 | - | 120 | A |
| | | full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$ | - | 132 | A |
| l ² t | I ² t for fusing | t _p = 10 ms; sine-wave pulse | - | 72 | A ² s |
| dI _T /dt | rate of rise of on-state current | I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s | - | 100 | A/µs |
| I _{GM} | peak gate current | t = 20 μs | - | 2 | Α |
| P _{GM} | peak gate power | | - | 5 | W |
| P _{G(AV)} | average gate power | over any 20 ms period | - | 0.5 | W |
| T _{stg} | storage temperature | | -40 | 150 | °C |
| T _j | junction temperature | | - | 125 | °C |
| V_{PP} | peak pulse voltage | T _j = 25 °C; non-repetitive, off-state; Fig. 6 | - | 2 | kV |

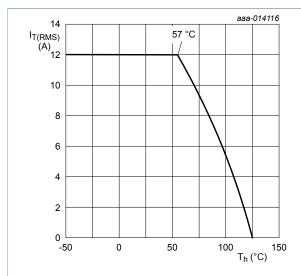
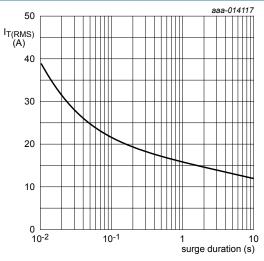


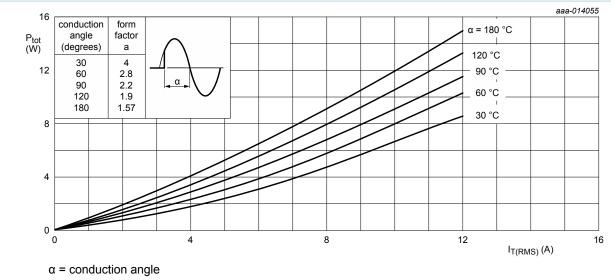
Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values



 $f = 50 \text{ Hz}; T_h = 57 ^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

AC Thyristor Triac power switch



 α = conduction angle a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

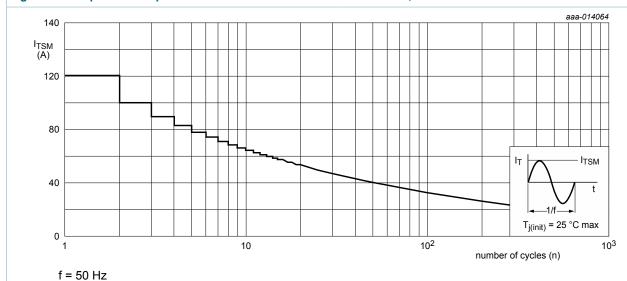


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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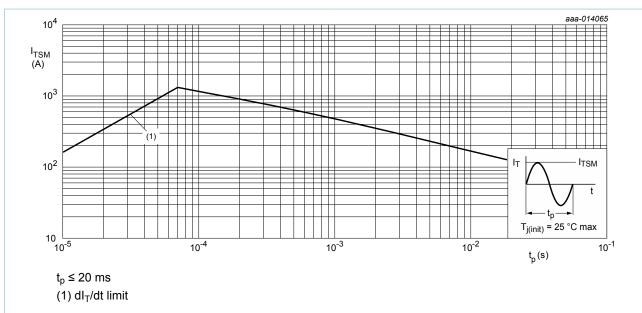


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

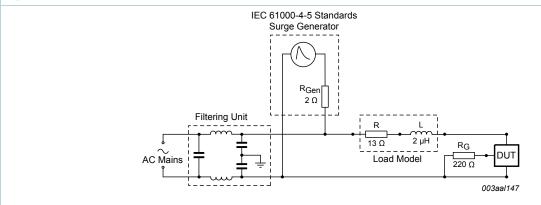
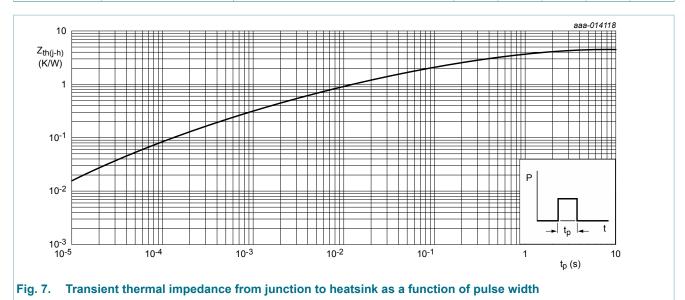


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| R _{th(j-h)} | thermal resistance from junction to heatsink | full cycle; with heatsink compound; Fig. 7 | - | - | 4.5 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 55 | - | K/W |



10. Isolation characteristics

Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|-----------------------|---|-----|-----|------|------|
| V _{isol(RMS)} | RMS isolation voltage | 50 Hz \leq f \leq 60 Hz; RH \leq 65% RH; T _h = 25 °C; from all terminals to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C _{isol} | isolation capacitance | f = 1 MHz; T _h = 25 °C; from main terminal 2 to external heatsink | - | 10 | - | pF |

11. Characteristics

Table 8 Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------------|---------------------------------------|---|------|------|-----|------|
| Static char | acteristics | | , | | | |
| I _{GT} | gate trigger current | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 8$ | - | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 8$ | - | - | 35 | mA |
| | | $V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$ | - | - | 35 | mA |
| I _L latching cu | latching current | $V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } Fig. 9$ | - | - | 50 | mA |
| | | $V_D = 12 \text{ V; } I_G = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; } Fig. 9$ | - | - | 70 | mA |
| | | $V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 9$ | - | - | 50 | mA |
| I _H | holding current | V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u> | - | - | 50 | mA |
| V _T | on-state voltage | I _T = 17 A; T _j = 25 °C; <u>Fig. 11</u> | - | 1.25 | 1.5 | V |
| V_{GT} | gate trigger voltage | V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12 | - | 0.8 | 1 | V |
| | | V _D = 400 V; I _T = 100 mA; T _j = 125 °C; Fig. 12 | 0.2 | 0.45 | - | V |
| I _D | off-state current | V _D = 800 V; T _j = 25 °C | - | - | 10 | μΑ |
| | | V _D = 800 V; T _j = 125 °C | - | - | 0.5 | mA |
| V _{CL} | clamping voltage | I_{CL} = 0.1 mA; t_p = 1 ms; T_j = 25 °C | 850 | - | - | V |
| Dynamic cl | naracteristics | | I | 1 | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 536 V; T _j = 125 °C; exponential waveform; gate open circuit | 3000 | - | - | V/µs |
| dl _{com} /dt | rate of change of commutating current | V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit | 14 | - | - | A/ms |

AC Thyristor Triac power switch

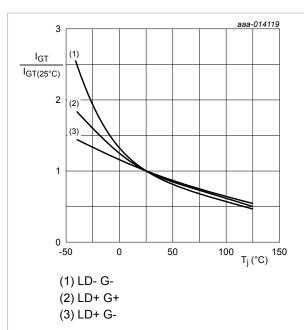


Fig. 8. Normalized gate trigger current as a function of junction temperature

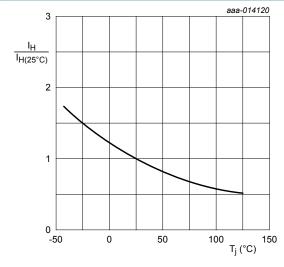


Fig. 10. Normalized holding current as a function of junction temperature

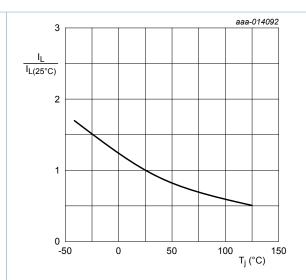
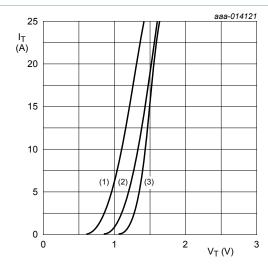


Fig. 9. Normalized latching current as a function of junction temperature



 $V_0 = 1.025 \text{ V}; R_s = 0.028 \Omega$

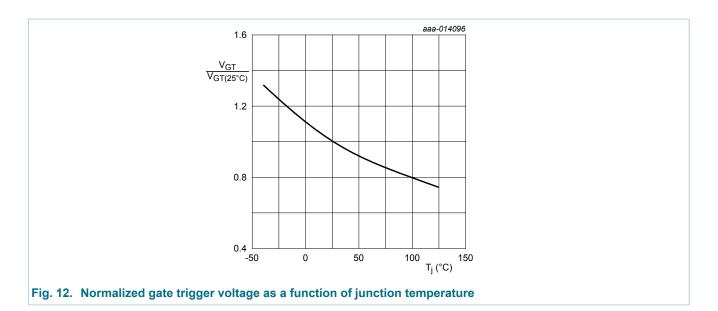
(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

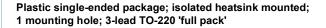
(3) T_i = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

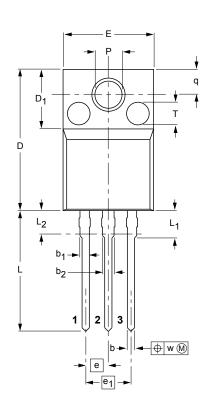
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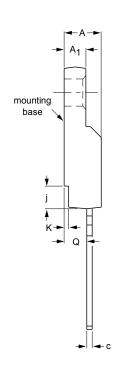


12. Package outline



SOT186A





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

| UNIT | Α | A ₁ | b | b ₁ | b ₂ | С | D | D ₁ | E | е | e ₁ | j | К | L | L ₁ | L ₂ ⁽¹⁾ max. | Р | Q | q | T ⁽²⁾ | w |
|------|------------|----------------|------------|----------------|----------------|------------|--------------|----------------|-------------|------|----------------|------------|------------|--------------|----------------|---------------------------------------|------------|------------|------------|------------------|-----|
| mm | 4.6 4.0 | 2.9 2.5 | 0.9 0.7 | 1.1 0.9 | 1.4 1.0 | 0.7 0.4 | 15.8 15.2 | 6.5 6.3 | 10.3 9.7 | 2.54 | 5.08 | 2.7 1.7 | 0.6 0.4 | 14.4 13.5 | 3.30 2.79 | 3 | 3.2 3.0 | 2.6 2.3 | 3.0 2.6 | 2.5 | 0.4 |

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

| OUTLINE | | EUROPEAN | ISSUE DATE | | |
|---------|-------------|----------------|------------|------------|-----------------------------------|
| VERSION | VERSION IEC | | JEITA | PROJECTION | ISSUE DATE |
| SOT186A | | 3-lead TO-220F | | | -02-04-09- 06-02-14 |

Fig. 13. Package outline TO-220F (SOT186A)

ACTT12X-800C

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